MOSFETs Silicon N-Channel MOS (DTMOSVI)

TK068N65Z5

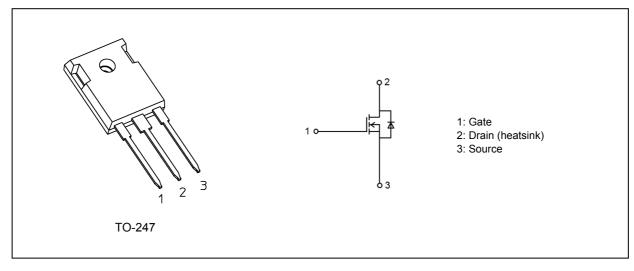
1. Applications

• Switching Voltage Regulators

2. Features

- (1) Fast reverse recovery time: $t_{rr} = 135$ ns (typ.)
- (2) Low drain-source on-resistance: $R_{DS(ON)} = 0.052 \ \Omega$ (typ.)
- (3) High-speed switching properties with the lower capacitance.
- (4) Enhancement mode: V_{th} = 3.5 to 4.5 V (V_{DS} = 10 V, I_{D} = 1.69 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25 \ ^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	650	V
Gate-source voltage		V _{GSS}	±30	
Drain current (DC)	(Note 1)	I _D	37	Α
Drain current (pulsed)	(Note 1)	I _{DP}	148	
Power dissipation (T _c = 25 °C)	PD	270	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	730	mJ
Single-pulse avalanche current		I _{AS}	7.4	A
Reverse drain current (DC)	(Note 1)	I _{DR}	37	
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	148	
Channel temperature		T _{ch}	150	ů
Storage temperature		T _{stg}	-55 to 150	
Mounting torque		TOR	0.8	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	0.462	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	50	

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: V_DD = 90 V, T_ch = 25 °C (initial), L = 23.6 mH, I_{AS} = 7.4 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V	_	_	±1	μA
Drain cut-off current	I _{DSS}	V_{DS} = 650 V, V_{GS} = 0 V	_	_	100	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	650	_	—	V
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 1.69 mA	3.5	_	4.5	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 18.5 A	_	0.052	0.068	Ω

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance		C _{iss}	V _{DS} = 300 V, V _{GS} = 0 V, f = 100 kHz	_	3765	_	pF
Reverse transfer capacitance		C _{rss}		_	3.0	_	
Output capacitance		C _{oss}]	_	92	_	
Effective output capacitance (energy related)	(Note 3)	C _{o(er)}	V_{DS} = 0 to 400 V, V_{GS} = 0 V		145	—	
Effective output capacitance (time related)	(Note 4)	C _{o(tr)}		_	970	—	
Gate resistance		r _g	V _{DS} = OPEN , f = 1 MHz	_	2.8	_	Ω
Switching time (rise time)		t _r	See Fig. 6.2.1	_	51	_	ns
Switching time (turn-on time)		t _{on}		_	92	_	
Switching time (fall time)		t _f]	_	3.5	_	
Switching time (turn-off time)		t _{off}]	_	115	_	
MOSFET dv/dt ruggedness		dv/dt	$V_{DS} \leq V_{DSS}, \ I_D \leq 18.5 \ A$	110	_	_	V/ns

Note 3: $C_{O(er)}$ is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0 V to 400 V. Note 4: $C_{O(tr)}$ is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 V to 400 V.

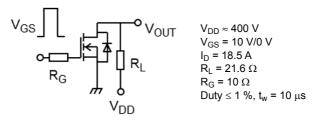


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400$ V, V_{GS} = 10 V, I_{D} = 37 A	—	68	-	nC
Gate-source charge 1	Q _{gs1}		_	23	_	
Gate-drain charge	Q _{gd}		_	22	_	

6.4. Source-Drain Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V _{DSF}	I _{DR} = 37 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time (Note	5) t _{rr}	V _{DD} = 400 V,	_	135	216	ns
Reverse recovery charge	Q _{rr}	I _{DR} = 18.5 A, V _{GS} = 0 V -dI _{DR} /dt = 100 A/μs	_	0.74	_	μC
Peak reverse recovery current	Irr	di <u>DR</u> /dt - 100 A/µS	_	11	—	A
Diode dv/dt ruggedness	dv/dt	$V_{DD} \leq 400$ V, $I_{DR} \leq 18.5$ A, V_{GS} = 0 V	70	_	_	V/ns

Note 5: Defined by design.

7. Marking (Note)

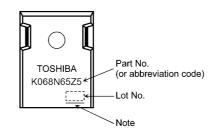


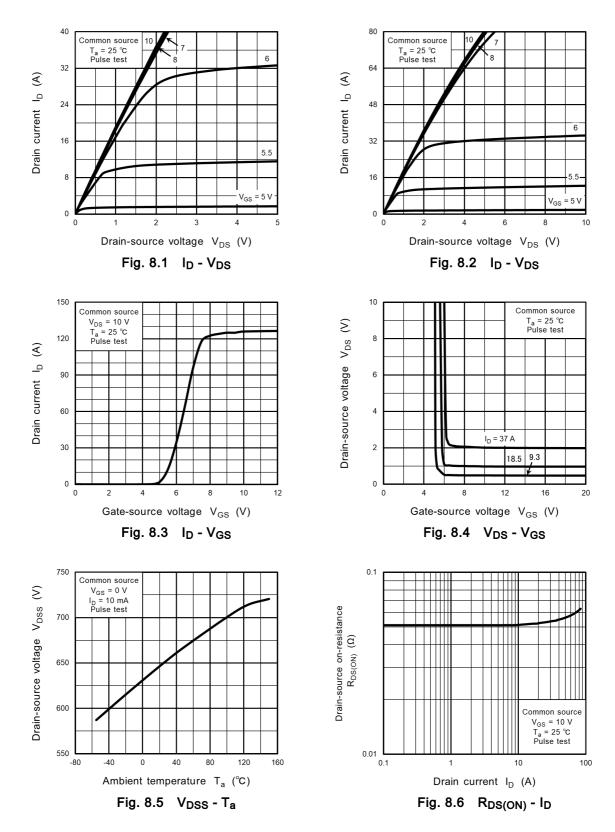
Fig. 7.1 Marking

 Note:
 A line under a Lot No. identifies the indication of product Labels.

 Not underlined: [[Pb]]/INCLUDES > MCV
 Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

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8. Characteristics Curves (Note)





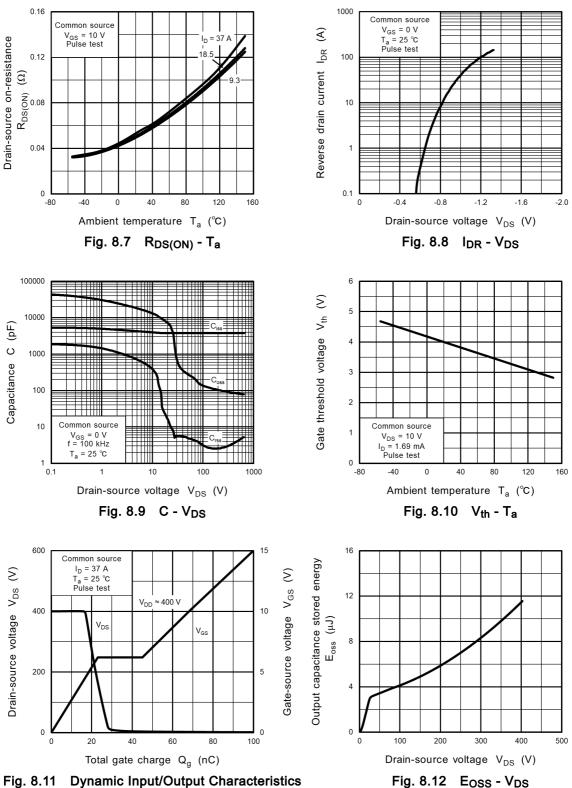
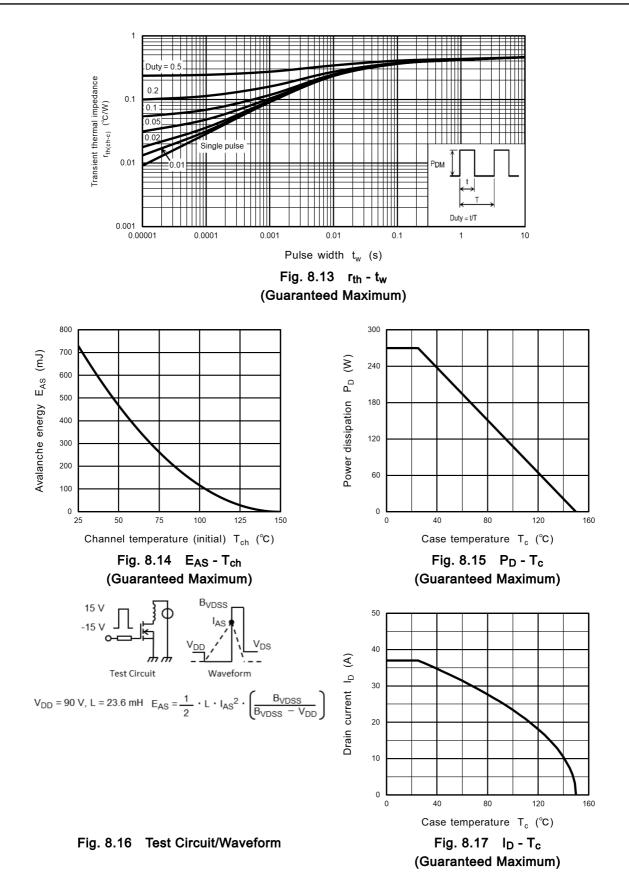
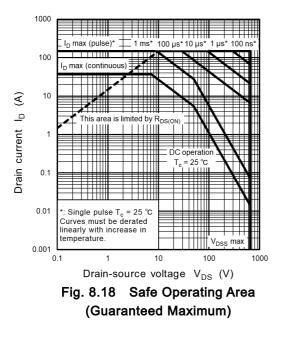


Fig. 8.11 **Dynamic Input/Output Characteristics**



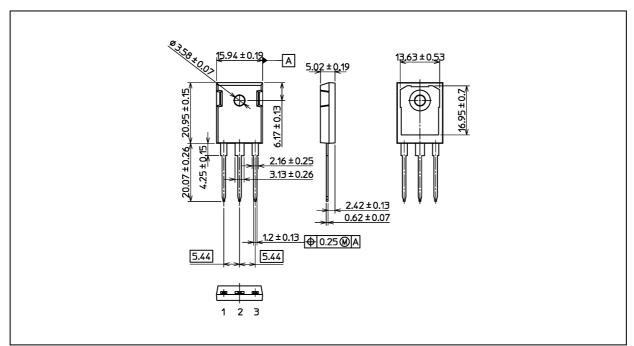


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

TK068N65Z5

Package Dimensions

Unit: mm



Weight: 6.15 g (typ.)

	Package Name(s)
TOSHIBA: 2-16L1A	
Nickname: TO-247	

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